

isc Silicon PNP Power Transistor

2SA1930

DESCRIPTION

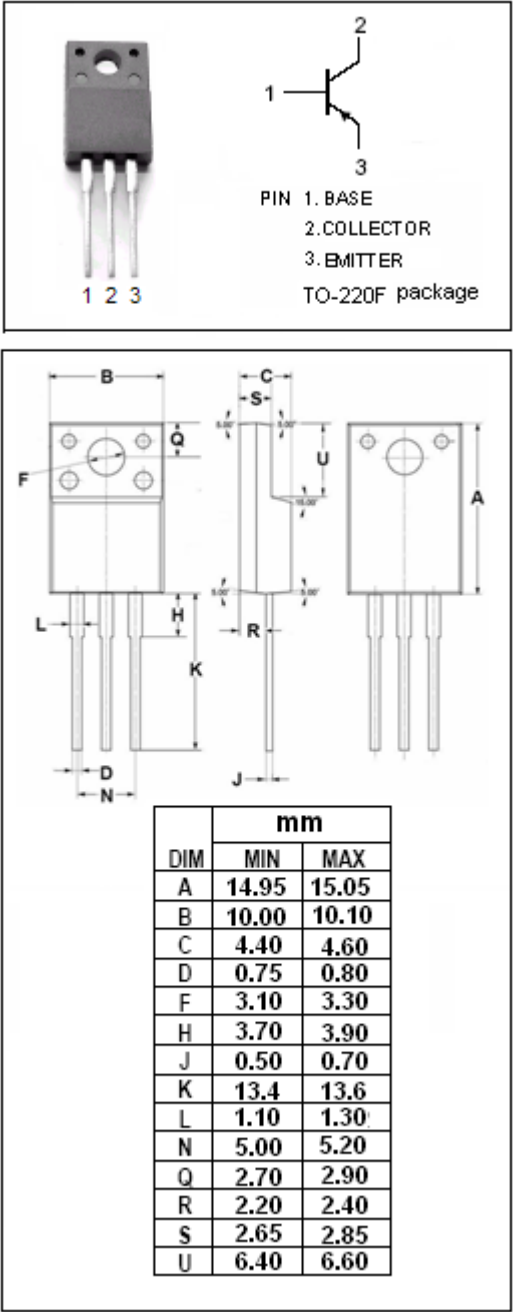
- High Transition Frenquency : $f_T=200\text{MHz(Typ.)}$
- Complementary to 2SC5171

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-180	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_B	Base Current-Continuous	-1	A
P_c	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	20	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon PNP Power Transistor**2SA1930****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -10\text{mA}$; $I_B = 0$	-180			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1.0\text{A}$; $I_B = -0.1\text{A}$			-1.0	V
$V_{BE(on)}$	Base-Emitter Voltage	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -180\text{V}$; $I_E = 0$			-5	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$			-5	μA
h_{FE-1}	DC Current Gain	$I_C = -0.1\text{A}$; $V_{CE} = -5\text{V}$	100		320	
h_{FE-2}	DC Current Gain	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$	50			
Cob	Collector Output Capacitance	$I_E = 0$; $V_{CB} = -10\text{V}$, $f=1\text{MHz}$		16		pF
f_T	Current-Gain—Bandwidth Product	$I_C = -0.3\text{A}$; $V_{CE} = -5\text{V}$		200		MHz